

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	-60	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = -10V	T _C = +25°C	I _D	-7.8	A
	T _C = +70°C	I _D	-6.3	A
	T _A = +25°C	I _D	-3.3	A
			-2.7	A
Pulsed Drain Current (380µs Pulse, 1% Duty Cycle)		I _{DM}	-24	A
Maximum Continuous Body Diode Forward Current (Note 6)		I _S	-1.8	A
Avalanche Current (Note 9) L = 0.1mH		I _{AS}	-19	A
Avalanche Energy (Note 9) L = 0.1mH		E _{AS}	18	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5 & 7)	T _A = +25°C	P _D	1.2	W
	T _A = +70°C		0.9	
Total Power Dissipation (Note 5 & 8)	T _A = +25°C		1.2	
Thermal Resistance, Junction to Ambient (Note 5 & 7)	Steady State	R _{ΘJA}	104	°C/W
	t < 10s		45	
Thermal Resistance, Junction to Ambient (Note 5 & 8)	Steady State		100	
Total Power Dissipation (Note 6 & 7)	T _A = +25°C	P _D	1.7	W
	T _A = +70°C		1.1	
Total Power Dissipation (Note 6 & 8)	T _A = +25°C		1.8	
Thermal Resistance, Junction to Ambient (Note 6 & 7)	Steady State	R _{ΘJA}	74	°C/W
	t < 10s		37	
Thermal Resistance, Junction to Ambient (Note 6 & 8)	Steady State		71	
Thermal Resistance, Junction to Case (Note 6 & 7)		R _{ΘJC}	15	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. For a dual device with one active die.
 8. For a device with two active die running at equal power.
 9. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 10)						
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1	μA	V _{DS} = -48V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	100	nA	V _{GS} = ±16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 10)						
Gate Threshold Voltage	V _{GS(TH)}	-1	—	-3	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	—	105	mΩ	V _{GS} = -10V, I _D = -4.5A
		—	—	130		V _{GS} = -4.5V, I _D = -3.5A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 11)						
Input Capacitance	C _{ISS}	—	969	—	pF	V _{DS} = -30V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	—	57	—	pF	
Reverse Transfer Capacitance	C _{RSS}	—	44	—	pF	
Gate Resistance	R _G	—	13.7	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _G	—	8.2	—	nC	V _{DS} = -30V, I _D = -12A
Total Gate Charge (V _{GS} = -10V)	Q _G	—	17.2	—	nC	V _{DS} = -30V, I _D = -12A
Gate-Source Charge	Q _{GS}	—	3.0	—	nC	
Gate-Drain Charge	Q _{GD}	—	3.1	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	4.4	—	ns	
Turn-On Rise Time	t _R	—	23	—	ns	V _{GS} = -10V, V _{DS} = -30V, R _{GEN} = 3Ω, I _D = -12A
Turn-Off Delay Time	t _{D(OFF)}	—	34	—	ns	
Turn-Off Fall Time	t _F	—	42	—	ns	I _S = -12A, di/dt = 100A/μs
Body Diode Reverse Recovery Time	t _{RR}	—	13.2	—	ns	
Body Diode Reverse Recovery Charge	Q _{RR}	—	6.18	—	nC	

Notes: 10. Short duration pulse test used to minimize self-heating effect.
11. Guaranteed by design. Not subject to product testing.

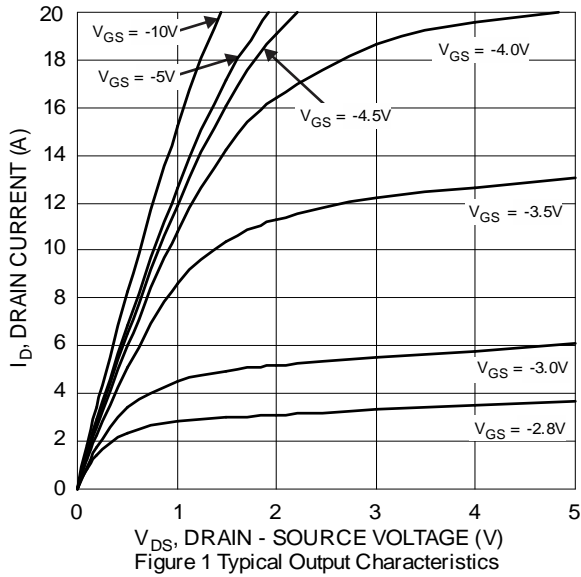


Figure 1 Typical Output Characteristics

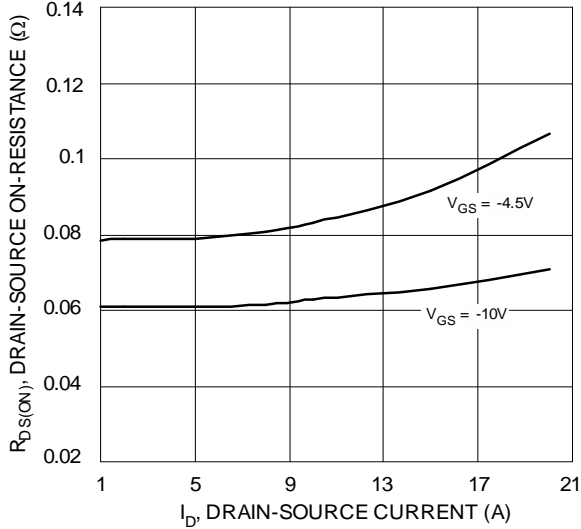


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

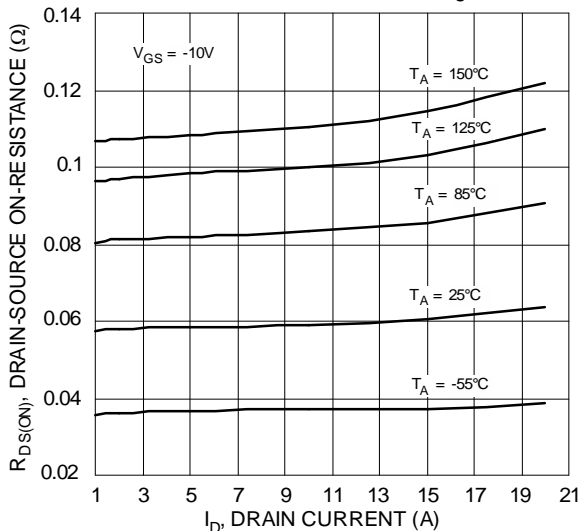


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

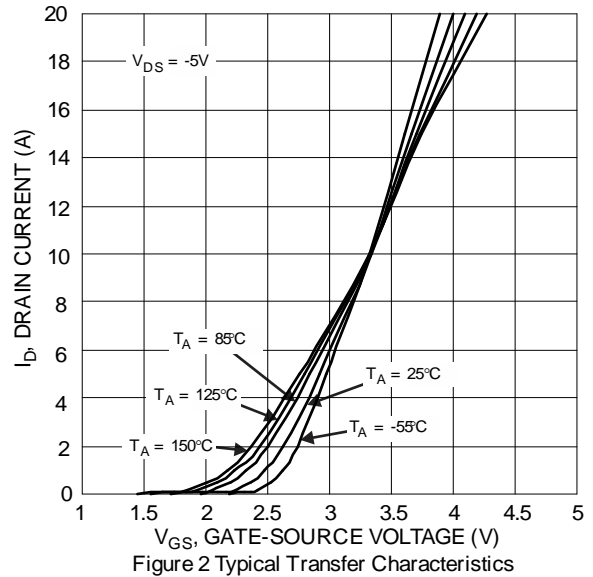


Figure 2 Typical Transfer Characteristics

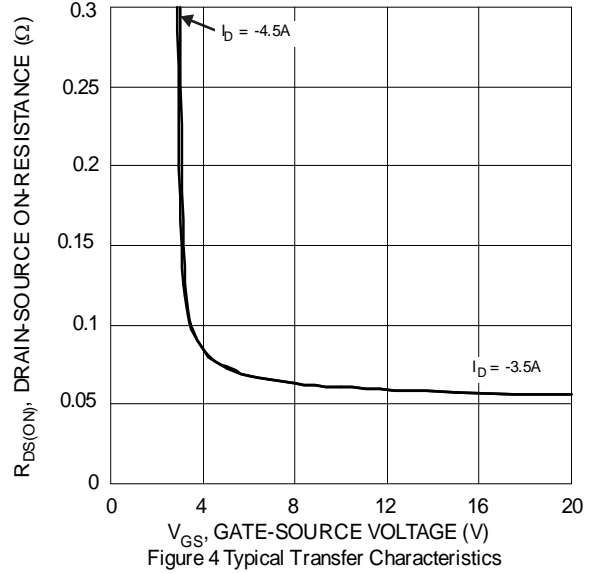


Figure 4 Typical Transfer Characteristics

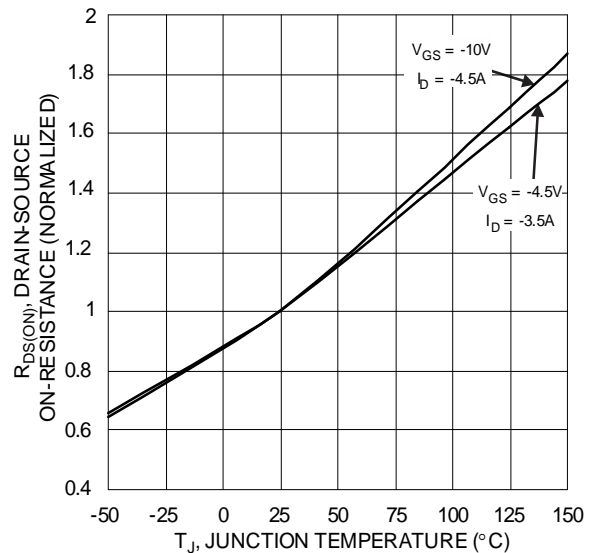
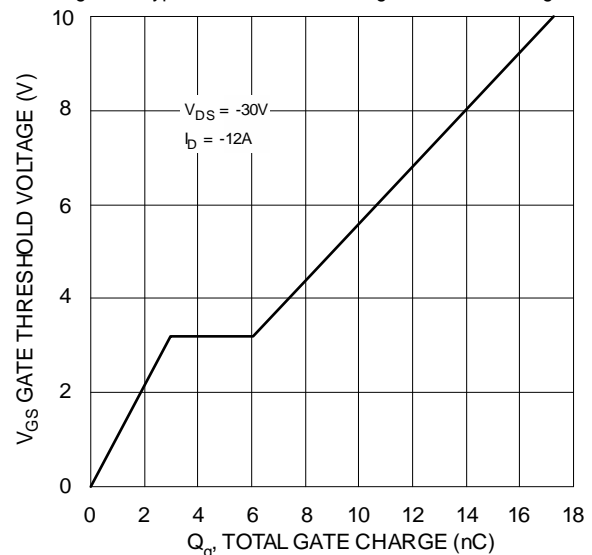
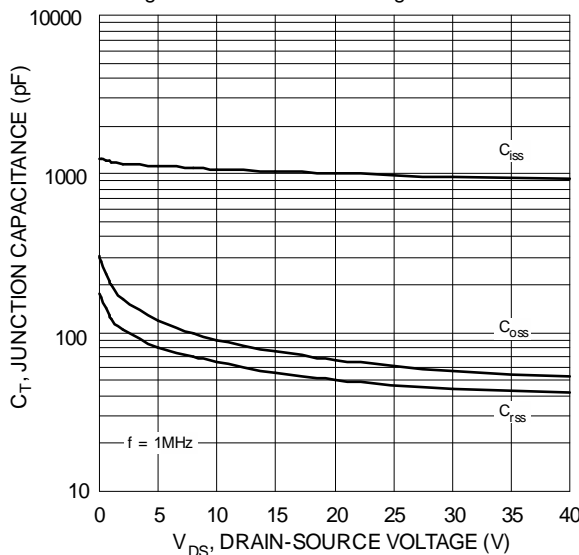
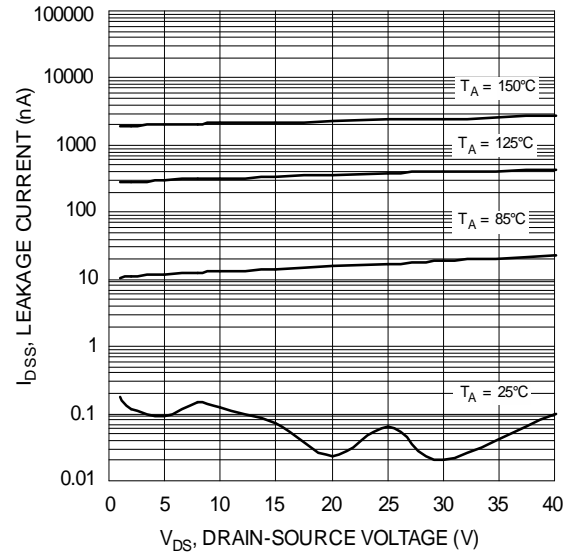
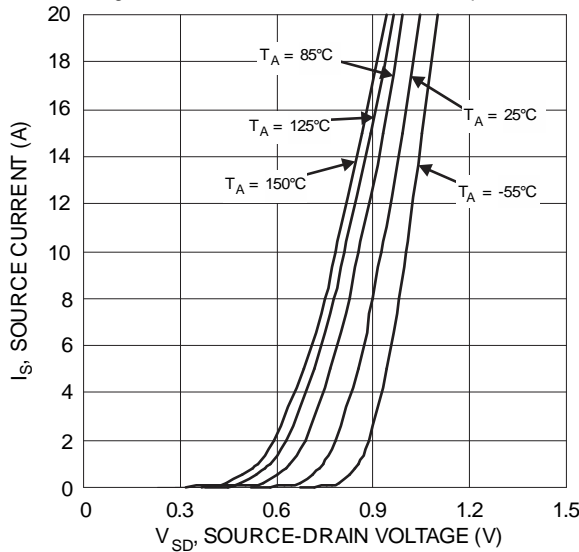
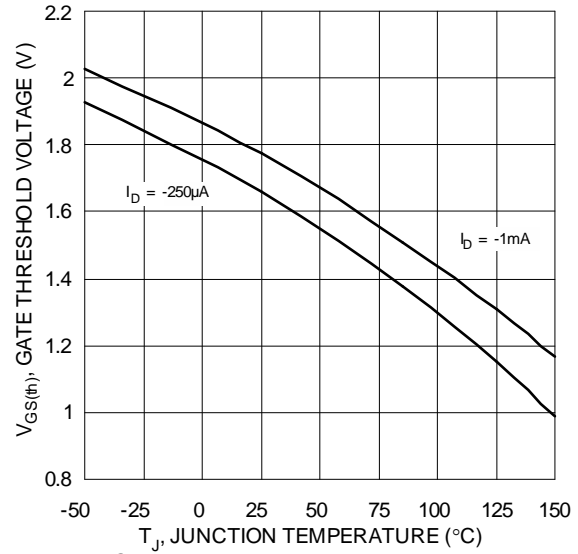
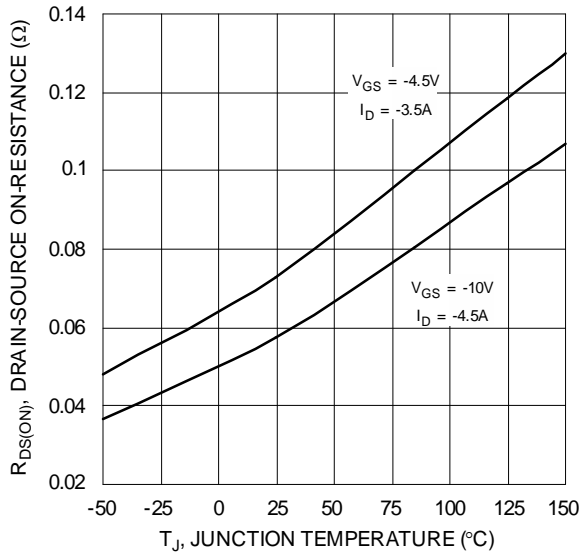


Figure 6 On-Resistance Variation with Temperature



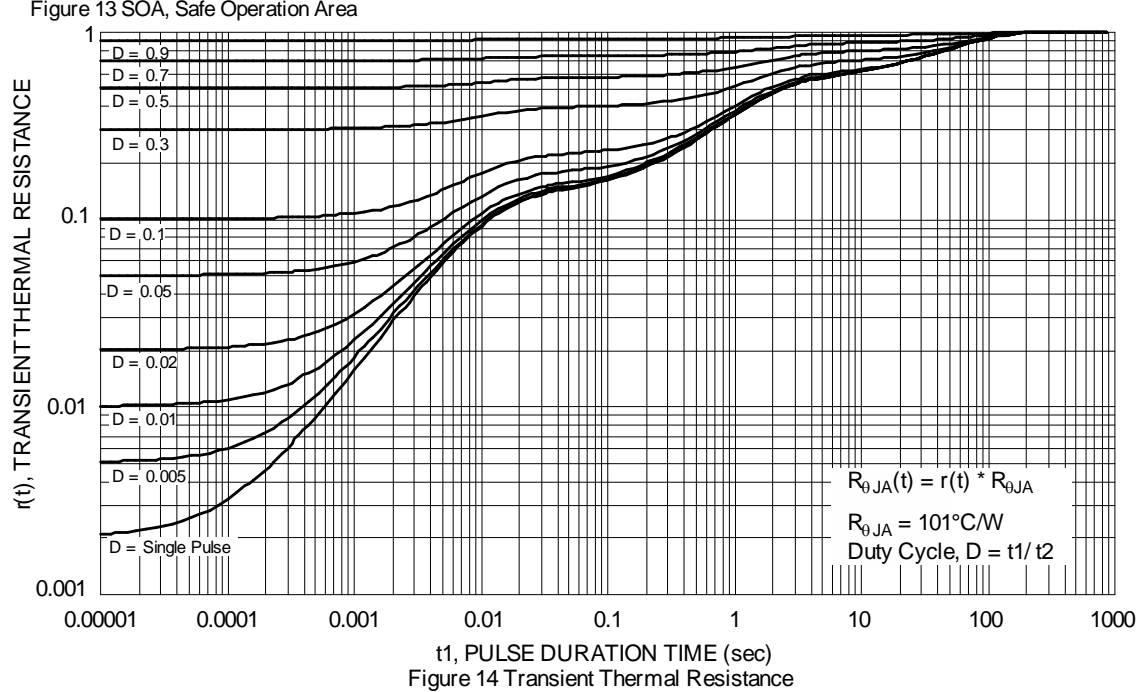
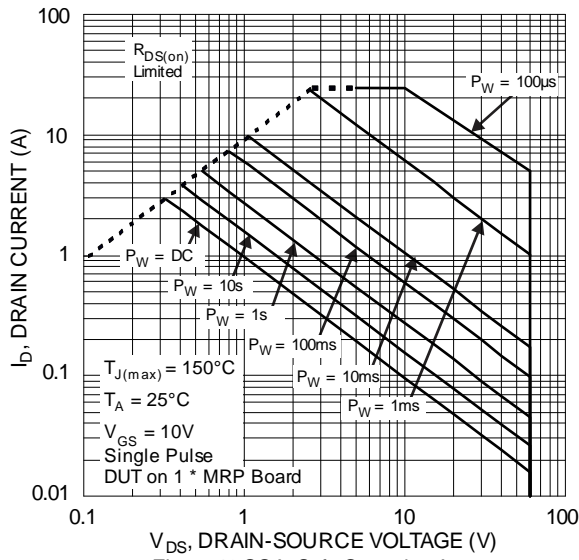
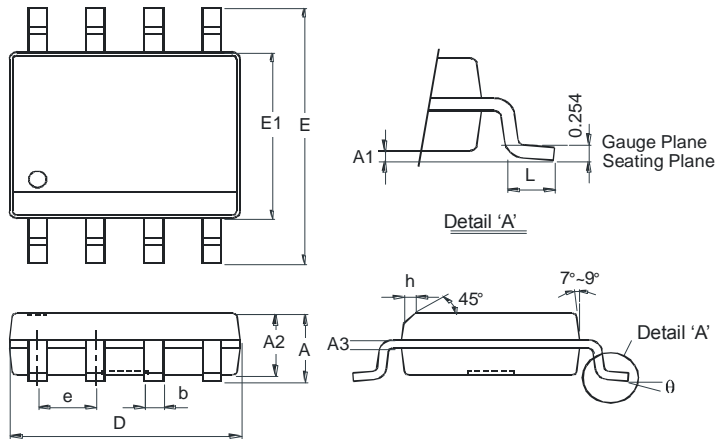


Figure 14 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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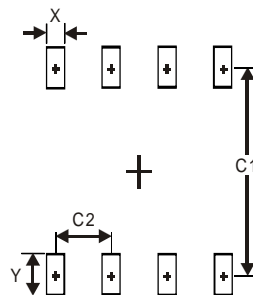


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Dim	Min	Max
A	—	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	—	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

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Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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